

CMLDM7585**SURFACE MOUNT SILICON
N-CHANNEL AND P-CHANNEL
ENHANCEMENT-MODE
COMPLEMENTARY MOSFET****SOT-563 CASE****APPLICATIONS:**

- Load/Power switches
- Power supply converter circuits
- Battery powered portable devices

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Drain-Source Voltage	
Gate-Source Voltage	
Continuous Drain Current (Steady State)	
Maximum Pulsed Drain Current ($t_p=10\mu\text{s}$)	
Power Dissipation (Note 1)	
Power Dissipation (Note 2)	
Power Dissipation (Note 3)	
Operating and Storage Junction Temperature	
Thermal Resistance (Note 1)	

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$)**SYMBOL TEST CONDITIONS**

I_{GSS}, I_{GSSR}	$V_{GS}=4.5\text{V}, V_{DS}=0$
I_{DSS}	$V_{DS}=16\text{V}, V_{GS}=0$
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$
V_{SD}	$V_{GS}=0, I_S=200\text{mA}$
V_{SD}	$V_{GS}=0, I_S=250\text{mA}$
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=600\text{mA}$
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=350\text{mA}$
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=500\text{mA}$
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=300\text{mA}$
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=350\text{mA}$
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=150\text{mA}$

www.centrasemi.com**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLDM7585 consists of complementary N-Channel and P-Channel enhancement-mode silicon MOSFETs designed for high speed pulsed amplifier and driver applications. These MOSFETs offer very low $r_{DS(ON)}$ and low threshold voltage.

MARKING CODE: 87C**FEATURES:**

- ESD protection up to 1800V (Human Body Model)
- 350mW power dissipation
- Very low $r_{DS(ON)}$
- Low threshold voltage
- Logic level compatible
- Small, SOT-563 surface mount package

SYMBOL	N-CH (Q1)	P-CH (Q2)	UNITS
V_{DS}	20		V
V_{GS}	8.0		V
I_D	650		mA
I_{DM}	1.3	1.0	A
P_D	350		mW
P_D	300		mW
P_D	150		mW
T_J, T_{stg}	-65 to +150		$^{\circ}\text{C}$
Θ_{JA}	357		$^{\circ}\text{C/W}$

N-CH (Q1)			P-CH (Q2)			UNITS
MIN	TYP	MAX	MIN	TYP	MAX	
-	-	1.0	-	-	10	μA
-	-	100	-	-	100	nA
20	-	-	20	-	-	V
0.5	-	1.1	0.5	-	1.0	V
-	-	1.1	-	-	-	V
-	-	-	-	-	1.1	V
-	0.14	0.23	-	-	-	Ω
-	-	-	-	0.25	0.36	Ω
-	0.2	0.275	-	-	-	Ω
-	-	-	-	0.37	0.5	Ω
-	-	0.7	-	-	-	Ω
-	-	-	-	-	0.8	Ω

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm²
 (2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm²
 (3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm²

R6 (8-June 2015)

CMLDM7585

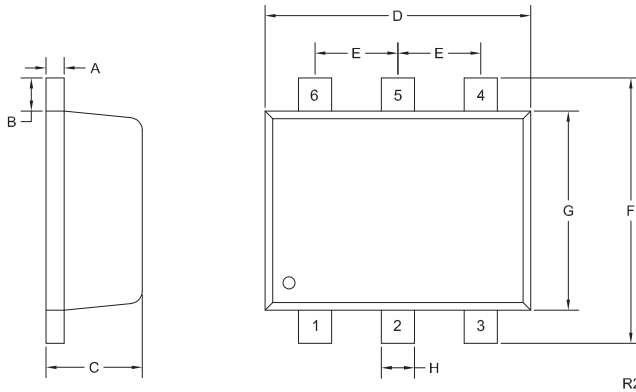
**SURFACE MOUNT SILICON
N-CHANNEL AND P-CHANNEL
ENHANCEMENT-MODE
COMPLEMENTARY MOSFET**



ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	N-CH (Q1)		P-CH (Q2)		UNITS
		MIN	TYP	MIN	TYP	
g_{FS}	$V_{DS}=10V, I_D=400mA$	1.0	-	-	-	S
g_{FS}	$V_{DS}=10V, I_D=200mA$	-	-	0.2	-	S
C_{rss}	$V_{DS}=16V, V_{GS}=0, f=1.0MHz$	-	18	-	25	pF
C_{iss}	$V_{DS}=16V, V_{GS}=0, f=1.0MHz$	-	100	-	100	pF
C_{oss}	$V_{DS}=16V, V_{GS}=0, f=1.0MHz$	-	16	-	21	pF
$Q_{g(tot)}$	$V_{DS}=10V, V_{GS}=4.5V, I_D=500mA$	-	1.58	-	-	nC
$Q_{g(tot)}$	$V_{DS}=10V, V_{GS}=4.5V, I_D=200mA$	-	-	-	1.2	nC
Q_{gs}	$V_{DS}=10V, V_{GS}=4.5V, I_D=500mA$	-	0.17	-	-	nC
Q_{gs}	$V_{DS}=10V, V_{GS}=4.5V, I_D=200mA$	-	-	-	0.24	nC
Q_{gd}	$V_{DS}=10V, V_{GS}=4.5V, I_D=500mA$	-	0.24	-	-	nC
Q_{gd}	$V_{DS}=10V, V_{GS}=4.5V, I_D=200mA$	-	-	-	0.36	nC
t_{on}	$V_{DD}=10V, V_{GS}=4.5V, I_D=200mA, R_G=10\Omega$	-	10	-	38	ns
t_{off}	$V_{DD}=10V, V_{GS}=4.5V, I_D=200mA, R_G=10\Omega$	-	25	-	48	ns

SOT-563 CASE - MECHANICAL OUTLINE

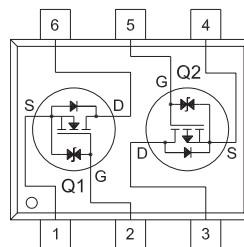


SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.059	0.067	1.50	1.70
G	0.043	0.051	1.10	1.30
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R2)

R2

PIN CONFIGURATION



LEAD CODE:

- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2
- 6) Drain Q1

MARKING CODE: 87C

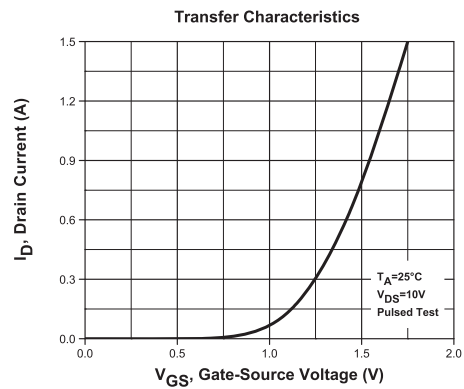
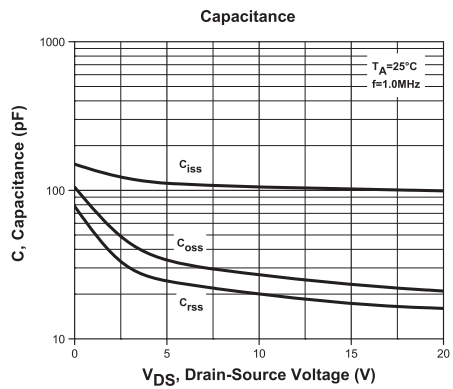
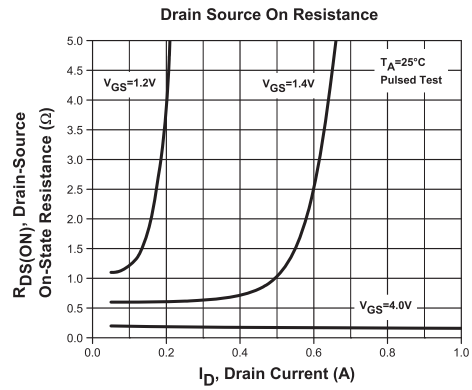
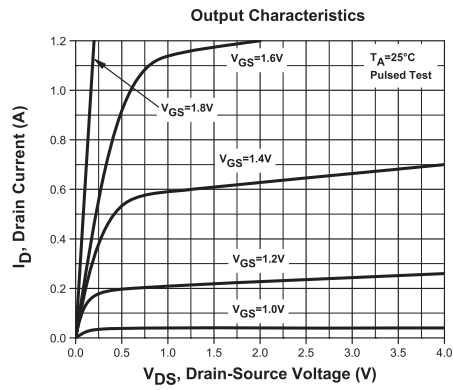
R6 (8-June 2015)

CMLDM7585

SURFACE MOUNT SILICON
N-CHANNEL AND P-CHANNEL
ENHANCEMENT-MODE
COMPLEMENTARY MOSFET



N-CHANNEL TYPICAL ELECTRICAL CHARACTERISTICS



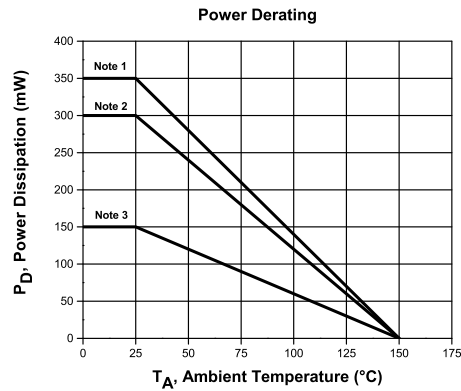
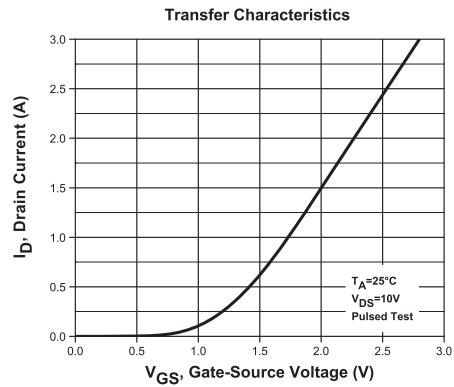
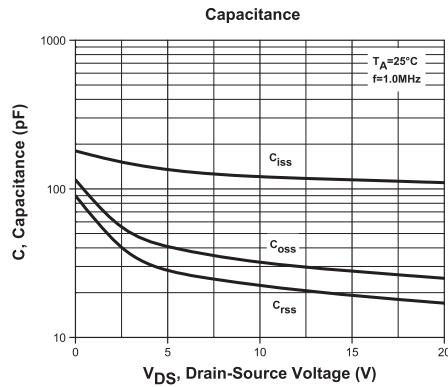
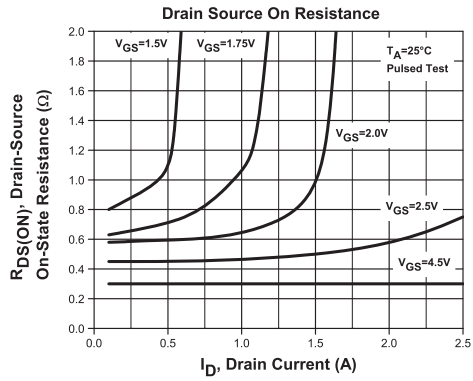
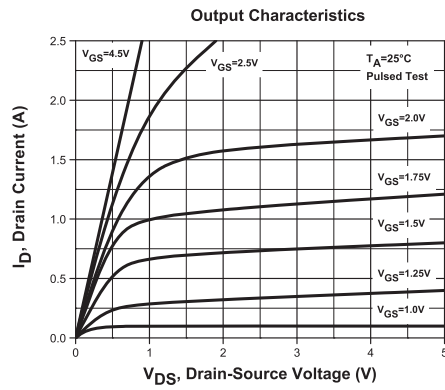
R6 (8-June 2015)

CMLDM7585

**SURFACE MOUNT SILICON
N-CHANNEL AND P-CHANNEL
ENHANCEMENT-MODE
COMPLEMENTARY MOSFET**



P-CHANNEL TYPICAL ELECTRICAL CHARACTERISTICS



R6 (8-June 2015)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
www.centrasemi.com/wwdistributors

For the latest version of Central Semiconductor's **LIMITATIONS AND DAMAGES DISCLAIMER**, which is part of Central's Standard Terms and Conditions of sale, visit: www.centrasemi.com/terms